Form PTO-1449 (Rev. 2-32) U.S. Department of Commerce Patent & Trademark Office	Atty. Docket No. Q76117	Serial No.: 10/600,833
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Applicant: Hiroyuki KIYOKU, *et al.*	Confirmation No.: ~~To be Assigned~~
IDS Filed 6/23/03	Filing Date: 06/23/03	Prior Art Group: ~~2823~~ 2826

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EXAMINER: [signature] **DATE CONSIDERED:** 4/6/05

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PTO/SB/08 A & B (modified)

Substitute for Form 1449 A & B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

IDS Filed 6/28/03

Sheet	4	of	4

Complete if Known	
~~Div. of~~ Application Number	10/600,833 ~~10/261,487~~
Confirmation Number	Unknown
Filing Date	June 23, 2003
First Named Inventor	KIYOKU, Hiroyuki
Prior Art Unit	~~2822~~ 2826
Prior Examiner Name	Stephen D. Meier
Attorney Docket Number	Q76117

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Examiner Initials*	Cite No.[1]	Document Number: Number	Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
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TD		US 6,362,515		03-2003	Hayakawa
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		US			
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Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3]	Number[4]	Kind Code[5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation[6]

OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation[6]

Examiner Signature		Date Considered	4/6/05

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